

$V_{RRM}$  = 650 V  
 $I_F (T_C=155^\circ\text{C})$  = 4 A  
 $Q_C$  = 12 nC

### Features

- Extremely low reverse current
- No reverse recovery current
- Temperature independent switching
- Positive temperature coefficient on  $V_F$
- Excellent surge current capability
- Low capacitive charge

### Benefits

- Essentially no switching losses
- System efficiency improvement over Si diodes
- Increased power density
- Enabling higher switching frequency
- Reduction of heat sink requirements
- System cost savings due to smaller magnetics
- Reduced EMI

### Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Motor drivers
- Power factor correction

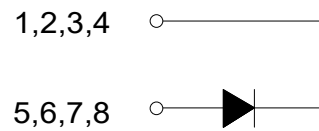
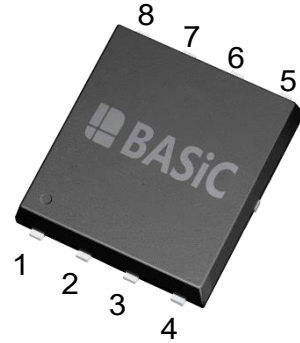
### Package Pin Definitions

- Pin1,2,3,4- Anode
- Pin5,6,7,8- Cathode

### Package Parameters

Part Number	Marking	Package
B2D04065D	B2D04065D	DFN 5*6

DFN 5\*6



**Maximum Ratings ( $T_c=25^\circ\text{C}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		650	V
$V_{RSM}$	Non-repetitive peak reverse voltage		650	V
$I_F$	Continuous forward current	$T_c=25^\circ\text{C}$ $T_c=155^\circ\text{C}$	15 4	A
$I_{FSM}$	Non-repetitive forward surge current	$T_c=25^\circ\text{C}$ , $t_p=10\text{ms}$ , Half Sine Wave	32	A
$\int j^2 dt$	$i^2t$ value	$T_c=25^\circ\text{C}$ , $t_p=10\text{ms}$	5.12	A <sup>2</sup> S
$P_{tot}$	Power dissipation	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	61 26	W
$T_j$	Operating junction temperature		-55~175	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~175	$^\circ\text{C}$

**Thermal Characteristics**

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		2.43		K/W

**Electrical Characteristics**
**Static Characteristics**

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{DC}$	DC blocking voltage	$T_j=25^{\circ}C$	650			V
$V_F$	Diode forward voltage	$I_F=4A$ $T_j=25^{\circ}C$ $I_F=4A$ $T_j=175^{\circ}C$		1.40 1.70		V
$I_R$	Reverse current	$V_R=650V$ $T_j=25^{\circ}C$ $V_R=650V$ $T_j=175^{\circ}C$		1 10		$\mu A$

**AC Characteristics**

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$Q_C$	Total capacitive charge	$V_R=400V$ $T_j=25^{\circ}C$ $Q_c = \int_0^{V_R} C(V)dV$		12		nC
$C$	Total capacitance	$V_R=1V$ $f=1MHz$ $V_R=300V$ $f=1MHz$ $V_R=600V$ $f=1MHz$		181 21.6 21.3		pF
$E_C$	Capacitance stored energy	$V_R=400V$		3		$\mu J$

Typical Performance

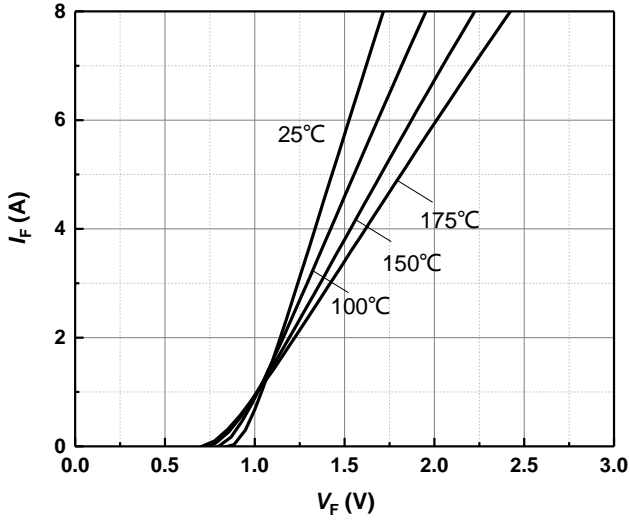


Figure 1. Typical forward characteristics

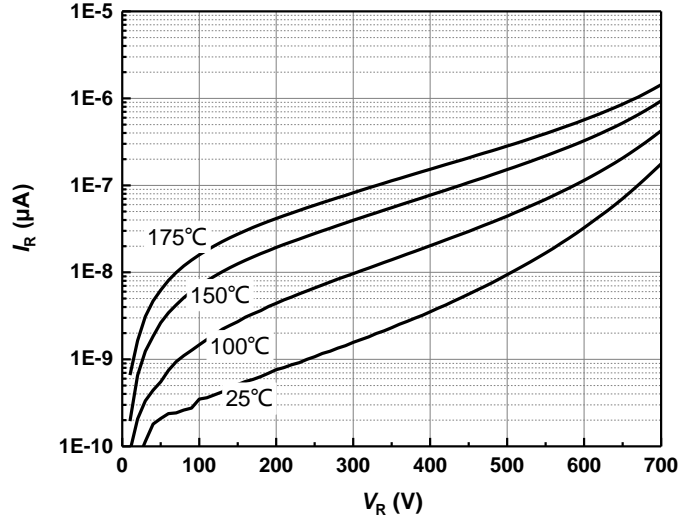


Figure 2. Typical reverse current as function of reverse voltage

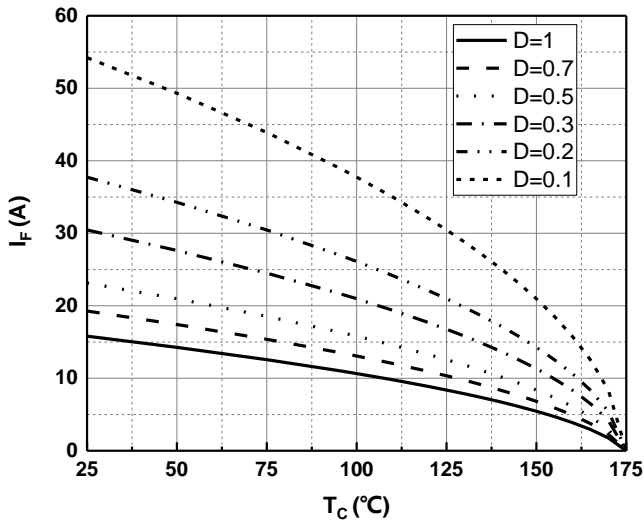


Figure 3. Diode forward current as function of temperature, D=duty cycle

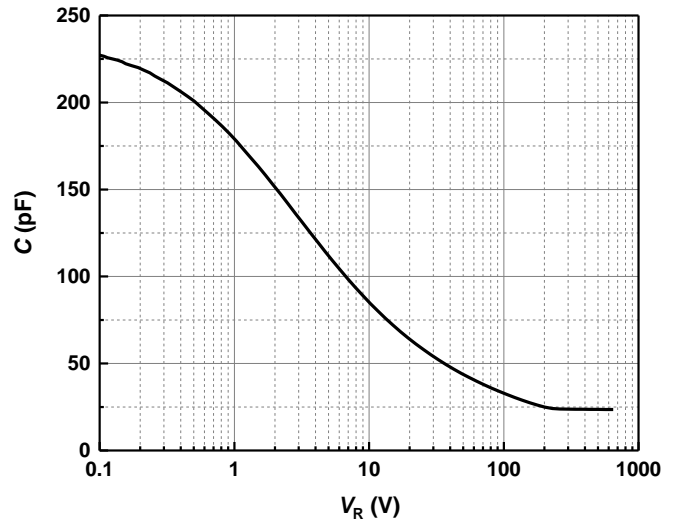


Figure 4. Typical capacitance as function of reverse voltage,  $C=f(V_R)$ ;  $T_j=25^{\circ}$ C;  $f=1$  MHz

Typical Performance

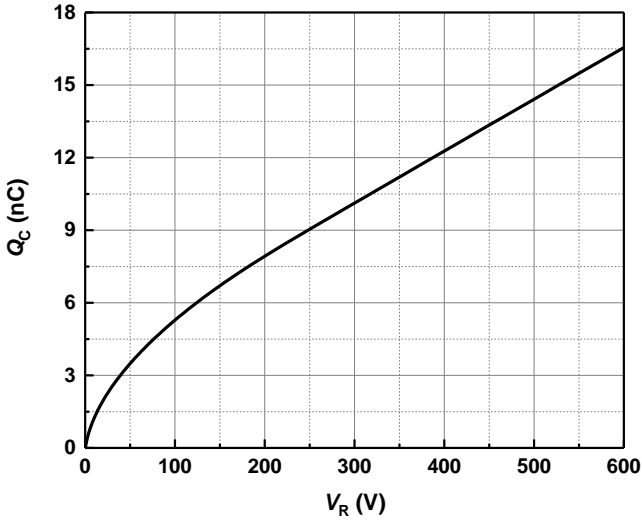


Figure 5. Typical reverse charge as function of reverse voltage

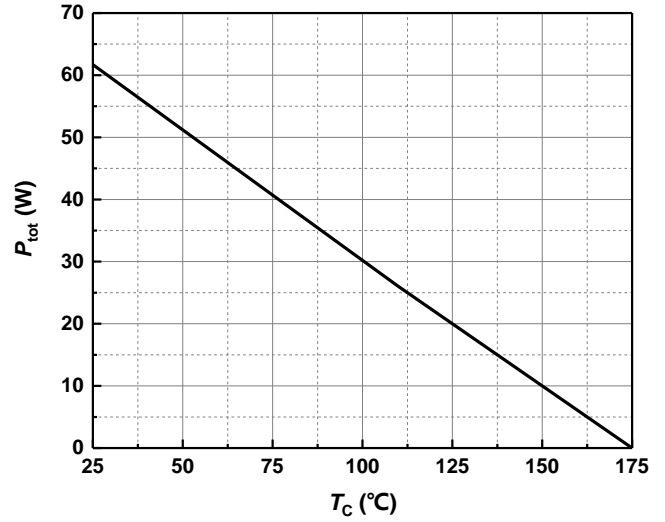


Figure 6. Power dissipation as function of case temperature

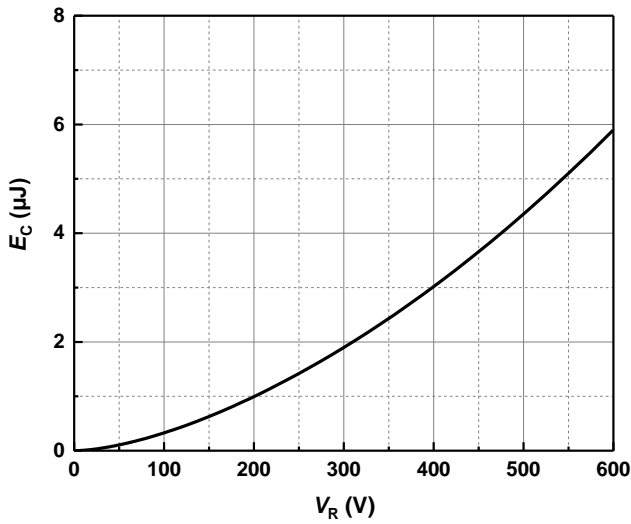


Figure 7. Capacitance stored energy

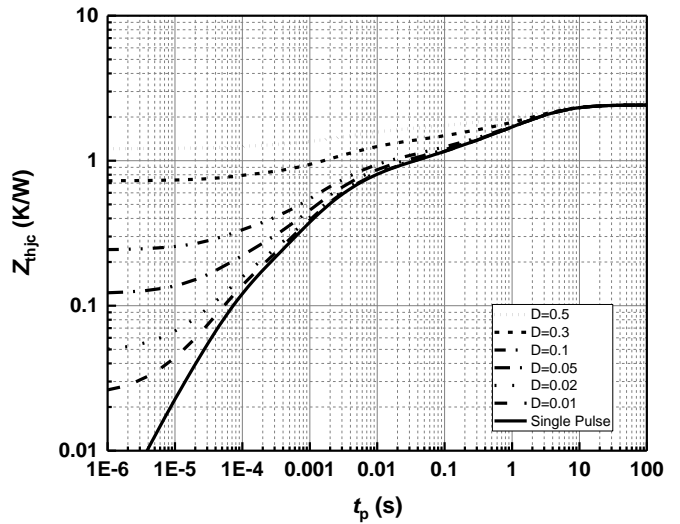
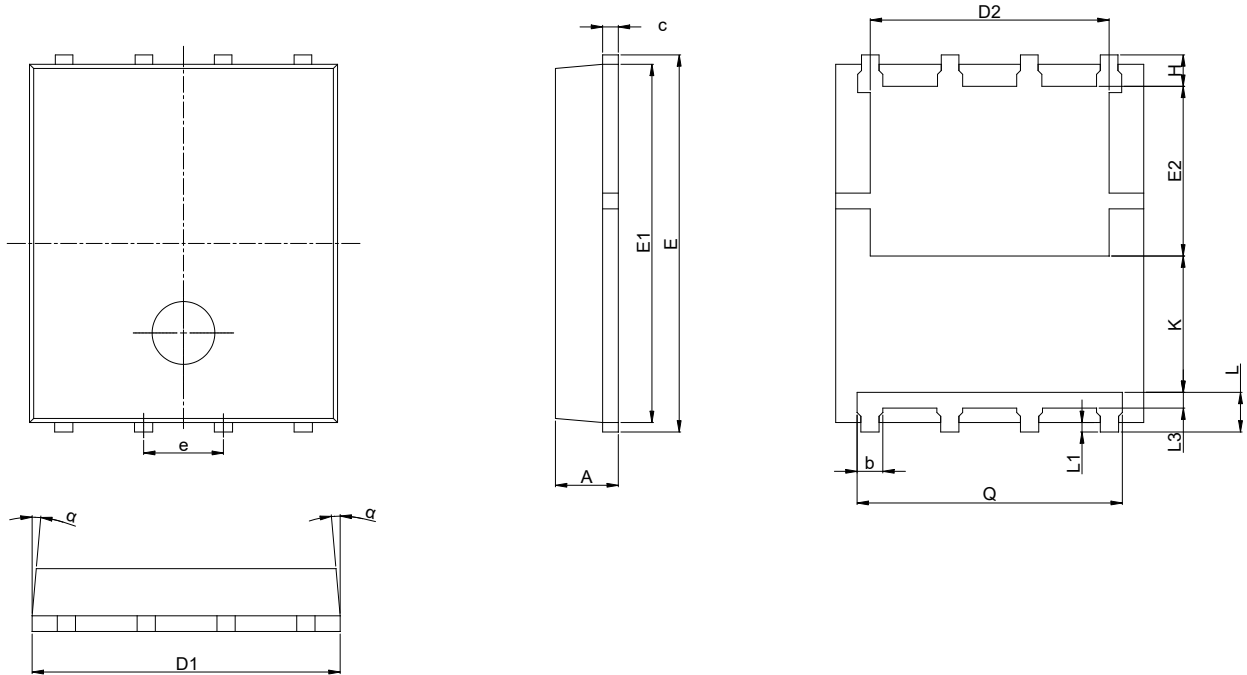


Figure 8. Max. transient thermal impedance,  $Z_{thjc} = f(t)$ , parameter:  $D = t / T$

**Package Dimensions**


SYMBOL	mm		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
c	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	2.66	2.76	2.86
e	1.27 BSC		
H	0.41	0.51	0.61
K	2.00	2.10	2.20
L	0.53	0.63	0.73
L1	0.06	0.13	0.20
L3	0.15	0.25	0.35
Q	4.12	4.22	4.32
α	0°	-	12°

**Revision History**

<b>Document Version</b>	<b>Date of Release</b>	<b>Description of Changes</b>
Rev. 0.0	2021-08-11	Release of the preliminary datasheet.

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